# 2SB0792 (2SB792), 2SB0792A (2SB792A)

## Silicon PNP epitaxial planar type

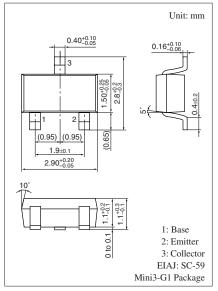
For high breakdown voltage low-noise amplification

### ■ Features

- High collector-emitter voltage (Base open) V<sub>CEO</sub>
- Low noise voltage NV
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage	2SB0792	V <sub>CBO</sub>	-150	V
(Emitter open)	2SB0792A		-185	
Collector-emitter voltage	2SB0792	V <sub>CEO</sub>	-150	V
(Base open)	2SB0792A		-185	
Emitter-base voltage (Coll	$V_{EBO}$	-5	V	
Collector current	$I_C$	-50	mA	
Peak collector current	$I_{CP}$	-100	mA	
Collector power dissipation	P <sub>C</sub>	200	mW	
Junction temperature	$T_{j}$	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	



Marking Symbol:

• 2SB0792: I

2SB0792A: 2F

## ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

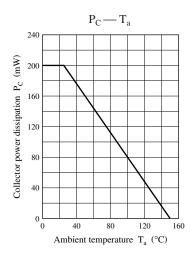
Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage	2SB0792	V <sub>CEO</sub>	$I_C = -100 \mu\text{A},  I_B = 0$	-150			V
(Base open)	2SB0792A			-185			
Emitter-base voltage (Collector open)		$V_{EBO}$	$I_E = -10 \ \mu A, I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)		$I_{CBO}$	$V_{CB} = -100 \text{ V}, I_E = 0$			-1	μΑ
Forward current transfer	2SB0792	$h_{FE}$	$V_{CE} = -5 \text{ V}, I_{C} = -10 \text{ mA}$	130		450	_
ratio *	2SB0792A			130		330	
Collector-emitter saturation voltage		V <sub>CE(sat)</sub>	$I_C = -30 \text{ mA}, I_B = -3 \text{ mA}$			-1	V
Transition frequency		$f_T$	$V_{CB} = -10 \text{ V}, I_E = 10 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance		C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		4		pF
(Common base, input open circuited)							
Noise voltage NV		$V_{CE} = -10 \text{ V}, I_{C} = -1 \text{ mA}, G_{V} = 80 \text{ dB}$		150		mV	
			$R_g = 100 \text{ k}\Omega$ , Function = FLAT				

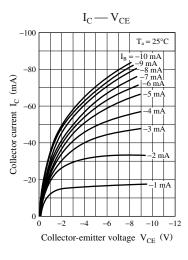
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

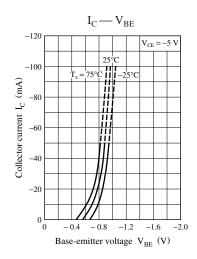
#### 2. \*: Rank classification

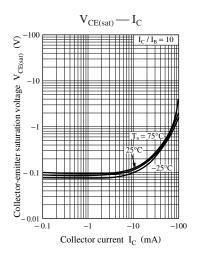
Rank		R	S	Т	
h	FE	130 to 220	185 to 330	260 to 450	
Marking	2SB0792	IR	IS	IT	
symbol	2SB0792A	2FR	2FS	_	

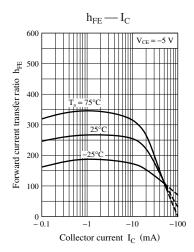
Note) The part numbers in the parenthesis show conventional part number.

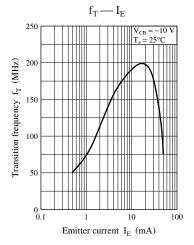


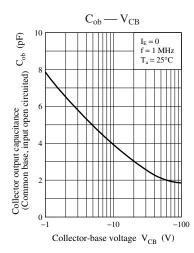












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